

IGBT Modules / SEMITOP

Type	IGBT						Diode			Rectifier		Module		Circuit	
	$I_C @ T_S = 25^{\circ}\text{C}$	I_{Cnom}	$V_{CE(sat)} @ T_J = 25^{\circ}\text{C typ.}$	E_{on}	E_{off}	$R_{th(j-a)}$	$I_F @ T_S = 25^{\circ}\text{C}$	$V_F @ T_J = 25^{\circ}\text{C typ.}$	E_{rr}	$R_{th(j-a)}$	$R_{th(j-a)}$	$I_{FSM} @ T_J = 25^{\circ}\text{C}$	Case		
	A	A	V	mJ	mJ	K/W	A	V	mJ	K/W	K/W	A			
600V - IGBT3 (Trench)															
SK 75 GB 066 T	77	75	1.45	3.1	2.8	0.94	62	1.35	0.85	1.55	-	-	3		
SK 100 GB 066 T	96	100	1.45	7	6	0.78	108	1.35	1.7	0.91	-	-	3		
SK 150 GB 066 T	124	150	1.45	6.25	5.7	0.55	135	1.35	1.7	0.73	-	-	3		
SK 30 GBB 066 T	40	30	1.45	0.97	1.77	1.65	36	1.45	0.26	2.1	-	-	3		
SK 50 GBB 066 T	60	50	1.45	2.2	1.73	1.11	56	1.50	0.72	1.7	-	-	3		
SK 75 GBB 066 T	77	75	1.45	3.1	2.8	0.94	77	1.35	0.85	1.55	-	-	3		
SK 20 MLI 066	30	20	1.45	0.4	1.07	1.95	30	1.60	0.2	2.46	-	-	3		
SK 30 MLI 066	40	30	1.45	0.97	1.77	1.65	37	1.50	0.26	2.3	-	-	3		
SK 30 MLI 066p ¹⁾	37	30	1.45	0.97	1.77	1.65	34	1.50	0.26	2.3	-	-	3p		
SK 50 MLI 066	60	50	1.45	1.46	2.02	1.11	56	1.50	1.07	1.7	-	-	3		
SK 75 MLI 066 T	83	75	1.45	1.7	2.8	0.75	92	1.50	1.1	1.2	-	-	4		
SK 100 MLI 066 T	105	100	1.45	2.5	4.2	0.65	110	1.35	1.9	0.9	-	-	4		
SK 150 MLI 066 T	151	150	1.45	2.7	5.9	0.55	115	1.50	2.6	0.72	-	-	4		
SK 20 GD 066 ET	30	20	1.45	0.34	0.63	1.95	31	1.45	0.2	2.46	-	-	3		
SK 30 GD 066 ET	40	30	1.45	0.97	1.77	1.65	36	1.45	0.26	2.1	-	-	3		
SK 50 GD 066 ET	60	50	1.45	2.2	1.73	1.11	56	1.50	0.72	1.7	-	-	3		
SK 50 GD 066 ETp ¹⁾	59	50	1.45	2.2	1.73	1.11	51	1.47	0.72	1.7	-	-	3p		
SK 30 GD 066 ETp ¹⁾	40	30	1.45	0.97	1.77	1.65	36	1.45	0.26	2.1	-	-	3p		
SK 75 GD 066 T	83	75	1.45	3.1	2.8	0.75	92	1.35	0.85	1.2	-	-	4		
SK 100 GD 066 T	105	100	1.45	7	6	0.65	99	1.30	1.7	0.8	-	-	4		
SK 150 GD 066 T	151	150	1.45	6.25	5.7	0.55	198	1.30	1.7	0.54	-	-	4		
SK 200 GD 066 T	174	200	1.45	13.9	12	0.45	99	1.30	3.4	0.8	-	-	4		
SK 20 DGD L 066 ET	30	20	1.45	0.3	0.6	1.95	27	1.40	0.2	2.46	2.15	220	3		
SK 30 DGD L 066 ET	40	30	1.45	0.55	1.15	1.65	36	1.50	0.53	2.3	1.7	370	3		
SK 50 DGD L 066 T	69	50	1.45	2.2	1.74	0.95	54	1.35	0.73	1.6	1.5	370	4		
SK 75 DGD L 066 T ³⁾	81	75	1.45	3.1	2.8	0.75	64	1.35	0.9	1.2	0.9	700	4		
SK 100 DGD L 066 T	106	100	1.45	4.4	3.5	0.65	99	1.10	1.45	0.8	0.9	700	4		
SK 50 DGD L 066 ETE2 ¹⁾	53	50	1.45	0.85	1.6	1.31	51	1.00	0.9	1.46	1.8	520	E2		

Footnotes: 1) Sample status / 2) In production new / 3) Not for new designs

IGBT Modules / SEMITOP

Type	IGBT						Diode			Rectifier		Module		Circuit		
	$I_C @ T_S = 25^{\circ}\text{C}$	I_{Cnom}	$V_{CE(sat)} @ T_J = 25^{\circ}\text{C typ.}$	E_{on}	E_{off}	$R_{th(j-a)}$	$I_F @ T_S = 25^{\circ}\text{C}$	$V_F @ T_J = 25^{\circ}\text{C typ.}$	E_{rr}	$R_{th(j-a)}$	$R_{th(j-a)}$	$I_{FSM} @ T_J = 25^{\circ}\text{C}$	Case			
	A	A	V	mJ	mJ	K/W	A	V	mJ	K/W	K/W	A				
600V - NPT IGBT (Standard)																
SK 45 GAL 063 ³⁾	45	50	2.10	1.4	1.2	1	57	1.45	0.25	1.2	-	-	2			
SK 45 GAR 063 ³⁾	45	50	2.10	1.4	1.2	1	57	1.45	0.25	1.2	-	-	2			
SK 45 GB 063 ³⁾	45	50	2.10	1.4	1.2	1	57	1.45	0.25	1.2	-	-	2			
SK 80 GB 063 ³⁾	81	100	2.10	4	3	0.6	79	1.40	1.2	0.9	-	-	3			
SK 80 GM 063 ³⁾	81	100	2.00	3	2.3	0.6	105	1.30	0.2	1.2	-	-	2			
SK 15 GH 063 ³⁾	20	15	2.00	0.71	0.4	1.9	20	1.45	0.45	1.2	-	-	2			
SK 25 GH 063 ³⁾	30	30	2.10	1.1	0.8	1.4	36	1.45	0.25	1.7	-	-	2			
SK 45 GH 063 ³⁾	45	50	2.10	1.4	1.2	1	57	1.30	0.9	1.2	-	-	3			
SK 13 GD 063 ³⁾	18	10	2.10	0.6	0.4	2	22	1.45	0.1	2.3	-	-	3			
SK 25 GD 063 ³⁾	30	30	2.10	1.3	0.9	1.4	36	1.45	0.25	1.7	-	-	3			
SK 45 GD 063 ³⁾	45	50	2.10	1.4	1.2	1	36	1.45	0.25	1.7	-	-	3			
SK 25 GAD 063 T ³⁾	30	30	2.10	1.3	0.9	1.4	36	1.45	0.25	1.7	-	-	3			
600V - NPT IGBT (Ultrafast)																
SK 50 GB 065 ³⁾	54	60	2.00	1.1	0.7	0.85	64	1.45	0.55	1.1	-	-	2			
SK 50 GAL 065 ³⁾	54	60	2.00	1.1	0.7	0.85	57	1.30	0.2	1.2	-	-	2			
SK 50 GAR 065 ³⁾	54	60	2.00	1.1	0.7	0.85	57	1.30	0.2	1.2	-	-	2			
SK 50 GAR L 065 F	54	60	1.70	1.03	0.8	0.85	82	1.70	0.45	2.3	-	-	2			
SK 50 GAR L 065 USA ³⁾	54	60	1.70	1.07	0.76	0.85	64	1.40	0.55	2.3	-	-	2			

Footnotes: 1) Sample status / 2) In production new / 3) Not for new designs

IGBT Modules / SEMITOP

Type	IGBT						Diode			Rectifier			Module	Circuit	
	I_C @ $T_J = 25^{\circ}\text{C}$	I_{Cnom}	$V_{CE(sat)}$ @ $T_J = 25^{\circ}\text{C typ.}$	E_{on}	E_{off}	$R_{th(j-a)}$	I_F @ $T_J = 25^{\circ}\text{C}$	V_F @ $T_J = 25^{\circ}\text{C typ.}$	E_{rr}	$R_{th(j-a)}$	$R_{th(j-a)}$	I_{FSM} @ $T_J = 25^{\circ}\text{C}$	Case		
	A	A	V	mJ	mJ	K/W	A	V	mJ	K/W	K/W	A			
600V - NPT IGBT (Ultrafast)															
SK 55 GARL 065 E ³⁾	54	60	1.70	1.1	0.76	0.85	36	1.45	0.9	1.7	-	-	3		
SK 75 GARL 065 E ³⁾	80	90	1.70	2.71	2.75	0.6	57	1.30	0.2	1.2	-	-	3		
SK 50 GH 065 F ³⁾	54	60	2.00	1.07	1.76	0.85	82	1.10	0.42	1.1	-	-	3		
SK 35 GD 065 ET ³⁾	45	50	2.00	1.3	0.6	1	36	1.90	0.9	1.7	-	-	3		
SK 10 BGD 065 ET ³⁾	17	6	2.00	0.18	0.13	2	22	1.30	0.18	2.3	2.7	220	3		
SK 9 BGD 065 ET ³⁾	12	6	2.00	0.22	0.12	2.6	20	1.35	0.31	2.7	2.15	220	3		
SK 9 DGD 065 ET ³⁾	12	6	2.00	0.22	0.12	2.6	20	1.35	0.31	2.7	2.15	220	3		
SK 20 DGD 065 ET ³⁾	26	20	2.00	0.66	0.4	1.7	25	1.60	-	1.7	1.7	370	3		
SK 10 DGD L 065 ET ³⁾	17	6	2.00	0.18	0.13	2	22	1.30	0.18	2.3	2.7	220	3		
SK 20 DGD L 065 ET ³⁾	24	20	2.00	0.69	0.39	1.7	25	1.60	-	1.7	2	220	3		
650V - IGBT3 (Trench)															
SK 75 GD 07E3 ETE2 ¹⁾	66	75	1.45	1.1	2.55	1.1	70	1.43	1.85	1.35	-	-	E2		
SK 50 GD 07E3 ETE1 ¹⁾	49	50	1.45	0.64	1.7	1.45	57	1.37	0.85	1.5	-	-	E1		
SK30GD07E3ETE1V1 ¹⁾	38	30	1.45	0.8	1.45	1.6	37	1.55	0.65	2.2	-	-	E1		
650V - IGBT3 (Fast Trench)															
SK 151 GALE 07F3 TUF ¹⁾	-	150	1.85	8.8	4	0.41	116	1.59	0.55	2.34	1.2	635	3		
SK 50 MLI 07F3 D1p ¹⁾	51	50	1.85	1	1.18	1.11	56	1.37	0.95	1.55	-	-	3p		
SK 100 MLI 07F3 TD1p ¹⁾	92	100	1.85	2	3.36	0.65	118	1.37	1.9	0.72	-	-	4p		
SK 150 MLI 07F3 TD1p ¹⁾	119	150	1.85	9.07	1.3	0.55	118	1.37	1.76	0.72	-	-	4p		

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Type	IGBT						Diode			Rectifier		Module		Circuit	
	$I_c @ T_s = 25^{\circ}\text{C}$	I_{cnom}	$V_{CE(sat)} @ T_j = 25^{\circ}\text{C typ.}$	E_{on}	E_{off}	$R_{th(j-s)}$	$I_F @ T_s = 25^{\circ}\text{C}$	$V_F @ T_j = 25^{\circ}\text{C typ.}$	E_{rr}	$R_{th(j-s)}$	$R_{th(j-s)}$	$I_{FSW} @ T_j = 25^{\circ}\text{C}$	Case		
	A	A	V	mJ	mJ	K/W	A	V	mJ	K/W	K/W	A			
1200V - IGBT4 (Trench)															
SK 25 GB 12T4 ²⁾	37	25	1.85	2.27	2.7	1.31	30	2.40	1.28	1.91	-	-	2		
SK 35 GB 12T4	44	35	1.85	3.27	3.3	1.21	38	2.30	1.46	1.55	-	-	2		
SK 50 GB 12T4 T ²⁾	71	50	1.85	8.3	5	0.9	50	2.20	2.15	1.24	-	-	3		
SK 75 GB 12T4 T	80	75	1.85	13.6	8.2	0.74	70	2.10	3.39	0.97	-	-	3		
SK 100 GB 12T4 T ²⁾	100	100	1.85	16.6	10	0.6	85	2.25	5.2	0.87	-	-	3		
SK 200 GB 12T4 Tp ¹⁾	210	200	1.80	13.6	22.1	0.28	190	2.20	13.4	0.35	-	-	4p		
SK 150 GAH 12T4 Tp ¹⁾	167	150	1.85	10.8	15.6	0.33	33	2.33	0.82	1.1	-	-	4p		
SK 25 GH 12T4 ²⁾	35	25	1.85	2.27	2.7	1.31	28	2.41	1.28	1.91	-	-	3		
SK 50 GH 12T4 T ²⁾	75	50	1.80	8.3	5	0.65	56	2.20	2.15	1.05	-	-	4		
SK 100 GH 12T4 T	126	100	1.80	16.6	10	0.43	102	2.20	5.2	0.62	-	-	4		
SK 35 MLI 12T4 p ¹⁾	43	35	1.85	1.6	3.27	1.21	38	2.30	1.73	1.55	-	-	3p		
SK 70 MLI 12T4 Tp ¹⁾	90	70	1.85	13.5	8.5	0.55	78	2.30	2.73	0.73	-	-	4p		
SK 10 GD 12T4 ET ²⁾	17	8	1.85	0.41	0.76	2.2	15	2.38	0.41	2.7	-	-	3		
SK 15 GD 12T4 ET	27	15	1.85	0.83	1.52	1.65	21	2.38	0.82	2.34	-	-	3		
SK 25 GD 12T4 ET	37	25	1.85	2.27	2.7	1.31	30	2.40	1.28	1.91	-	-	3		
SK 25 GD 12T4 ETp ¹⁾	35	25	1.85	2.27	2.7	1.31	28	2.41	1.28	1.91	-	-	3p		

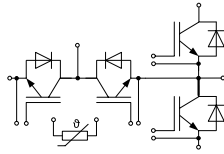
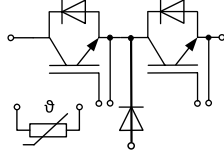
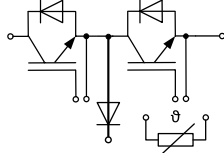
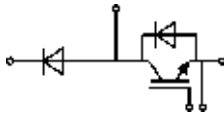
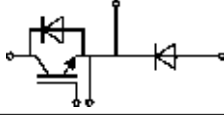
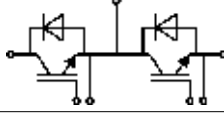
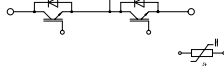
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	$I_c @ T_s = 25^{\circ}\text{C}$	I_{Cnom}	$V_{CE(sat)} @ T_j = 25^{\circ}\text{C typ.}$	E_{on}	E_{off}	$R_{th(j-a)}$	$I_f @ T_s = 25^{\circ}\text{C}$	$V_f @ T_j = 25^{\circ}\text{C typ.}$	E_{rr}	$R_{th(j-a)}$	$R_{th(j-a)}$	$I_{FSM} @ T_j = 25^{\circ}\text{C}$	Case		
	A	A	V	mJ	mJ	K/W	A	V	mJ	K/W	K/W	A			
1200V - IGBT4 (Trench)															
SK 35 GD 12T4 ET ²⁾	44	35	1.85	3.27	3.3	1.21	40	2.30	1.46	1.55	-	-	3		
SK 50 GD 12T4 T	75	50	1.85	8.3	5	0.65	60	2.20	2.15	0.97	-	-	4		
SK 50 GD 12T4 Tp ²⁾	72	50	1.85	8.3	5	0.65	60	2.22	2.15	0.97	-	-	4p		
SK 75 GD 12T4 T	102	75	1.85	13.6	8.2	0.51	83	2.20	3.38	0.75	-	-	4		
SK 75 GD 12T4 Tp ¹⁾	97	75	1.85	13.6	8.2	0.51	83	2.17	3.38	0.75	-	-	4p		
SK 100 GD 12T4 T	126	100	1.85	16.6	10	0.43	102	2.25	5.2	0.62	-	-	4		
SK 10 DGD 12T4 ET	17	8	1.85	0.41	0.75	2.2	15	2.38	0.41	2.7	2	220	3		
SK 15 DGD 12T4 ET	27	15	1.85	0.82	1.52	1.65	21	2.38	0.82	2.34	2	220	3		
SK 25 DGD 12T4 T	45	25	1.85	2.27	2.7	0.96	30	2.40	-	1.7	1.25	370	4		
SK 25 DGD 12T4 ETE2 ¹⁾	33	25	1.85	2.6	2.35	1.45	53	1.00	2.05	1.46	1.8	520	E2		
SK 35 DGD 12T4 T	58	35	1.85	3.27	3.3	0.8	46	2.30	1.46	1.37	1.25	370	4		
SK 35 DGD 12T4 ETE2 ¹⁾	43	35	1.85	3.15	3.2	1.2	53	1.00	2.6	1.46	1.55	520	E2		
SK 50 DGD 12T4 T	75	50	1.85	8.3	5	0.65	60	2.22	2.15	0.97	0.9	700	4		
SK25GD12T4ETE1 ¹⁾	33	25	1.85	2.6	2.35	1.45	29	2.41	2.05	1.8	-	-	E1		
SK35GD12T4ETE1 ¹⁾	43	35	1.85	3.15	3.2	1.2	38	2.30	2.6	1.55	-	-	E1		
SK50GD12T4ETE2 ¹⁾	66	50	1.85	5.8	4.5	0.75	59	2.22	3.6	0.98	-	-	E2		
SK75GD12T4ETE2 ¹⁾	84	75	1.85	8	6.4	0.65	82	2.17	5.5	0.77	-	-	E2		
1200V - IGBT4 (Fast Trench)															
SK 120 GB 12F4 T ¹⁾	174	120	2.05	8.8	7.47	0.22	29	2.38	2.04	1.25	-	-	3		
SK80TMLI12F4Tp ¹⁾	88	80	2.05	1.9	2.04	0.54	83	2.17	1.6	0.75	-	-	3p		
SK 150 TMLI 12F4 Tp ²⁾	180	150	2.05	3.13	5.29	0.24	100	2.20	4.8	0.65	-	-	4p		

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	$I_c @ T_s = 25^{\circ}\text{C}$	I_{cnom}	$V_{CE(sat)} @ T_j = 25^{\circ}\text{C typ.}$	E_{on}	E_{off}	$R_{th(j-s)}$	$I_F @ T_s = 25^{\circ}\text{C}$	$V_F @ T_j = 25^{\circ}\text{C typ.}$	E_{rr}	$R_{th(j-s)}$	$R_{th(j-s)}$	$I_{FSM} @ T_j = 25^{\circ}\text{C}$	Case		
	A	A	V	mJ	mJ	K/W	A	V	mJ	K/W	K/W	A			
1200V - IGBT4 (Fast Trench)															
SK 200 TML1 12F4 TE2 ¹⁾	147	200	2.05	7.2	4.5	0.4	67	2.17	4	1.05	-	-	E2		
SK 150 MLIT 12F4 TE2 ¹⁾	149	150	2.05	12.6	11	0.33	80	2.20	8.3	0.91	-	-	E2		
SK 150 MLIB 12F4 TE2 ¹⁾	149	150	2.05	12.6	11	0.33	80	2.20	8.3	0.91	-	-	E2		
1200V - NPT IGBT (Ultrafast)															
SK 60 GAL 125 ³⁾	51	50	3.20	8.36	3.32	0.6	43	2.00	2	1.16	-	-	2		
SK 60 GAR 125 ³⁾	51	50	3.20	8.36	3.32	0.6	43	2.00	2	1.16	-	-	2		
SK 60 GB 125	51	50	3.20	8.36	3.32	0.6	57	2.00	2	0.9	-	-	3		
SK 80 GB 125 T	85	75	3.20	9.9	5	0.32	90	2.00	1	0.65	-	-	3		

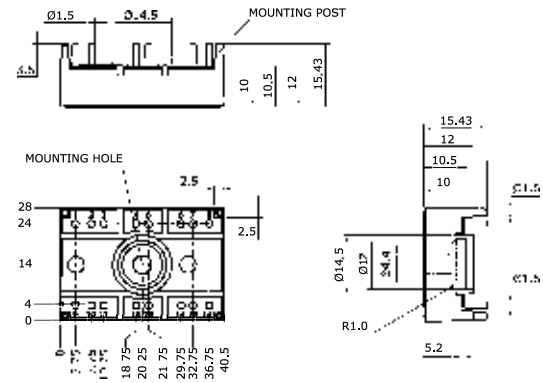
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IGBT Modules / SEMITOP

Cases

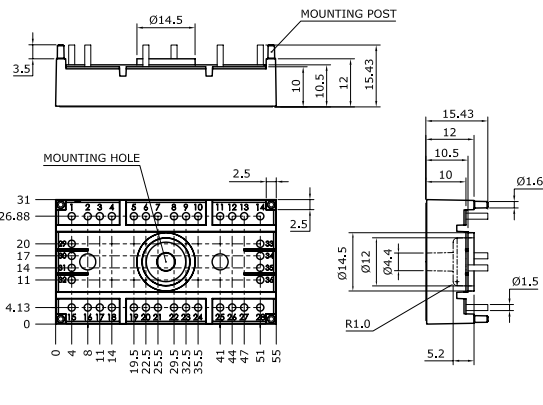
SEMISTOP 2

Dimensions: mm
Tolerance system: ISO 2768-m



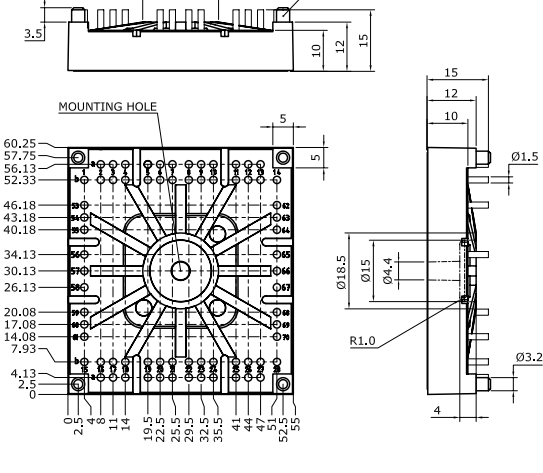
SEMISTOP 3

Dimensions: mm
Tolerance system: ISO 2768-m



SEMISTOP 4

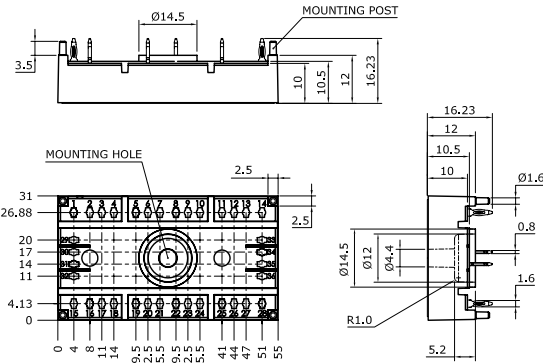
Dimensions: mm
Tolerance system: ISO 2768-m



Dimensions in mm

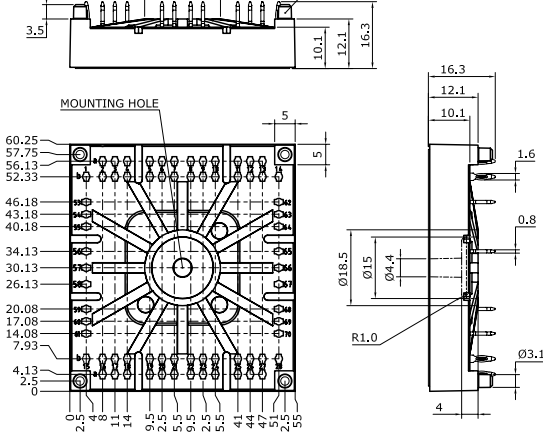
SEMISTOP 3 Press-Fit

Dimensions: mm
Tolerance system: ISO 2768-m



SEMISTOP 4 Press-Fit

Dimensions: mm
Tolerance system: ISO 2768-m

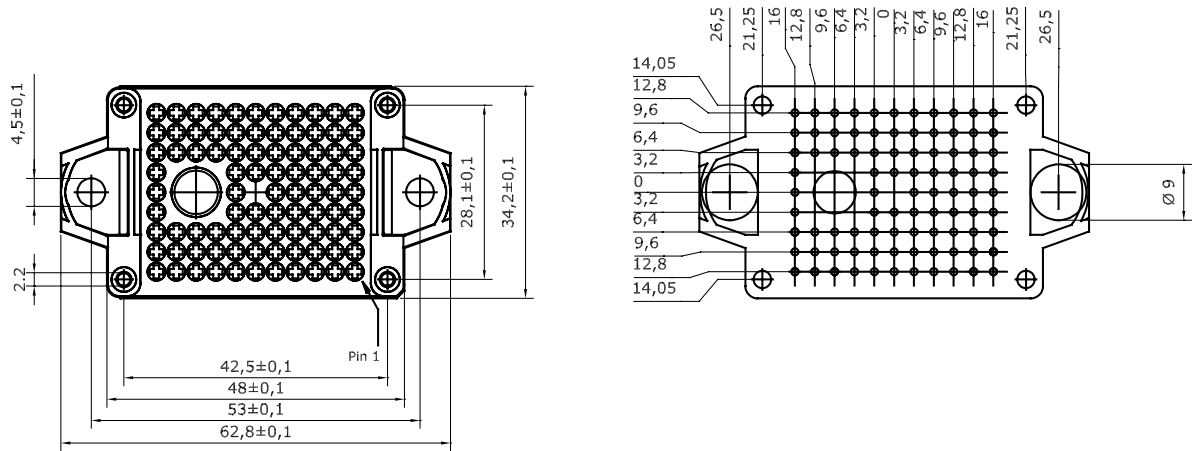


IGBT Modules / SEMITOP

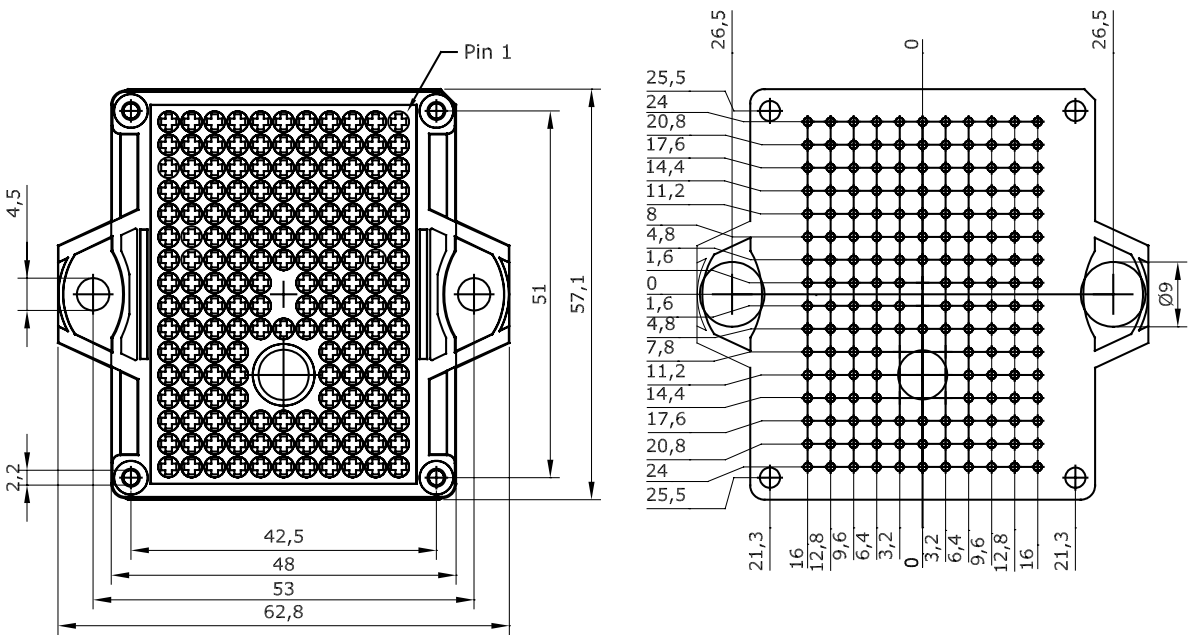
IGBT Modules / SEMiX

Cases

SEMISTOP E1



SEMISTOP E2



Dimensions in mm

Type	IGBT						Diode				Module		
	$I_c @ T_c = 25^{\circ}\text{C}$	I_{Cnom}	$V_{CE(sat)} @ T_j = 25^{\circ}\text{C typ.}$	E_{on}	E_{off}	$R_{th(j-c)}$	$I_F @ T_c = 25^{\circ}\text{C}$	$V_F @ T_j = 25^{\circ}\text{C typ.}$	E_{rr}	$R_{th(j-c)}$	Case	$R_{th(c-s)}$	
	A	A	V	mJ	mJ	K/W	A	V	mJ	K/W		K/W	Circuit
600V - IGBT3 (Trench)													
SEMiX402GAL066HDs	502	400	1.45	22	24	0.12	543	1.40	10	0.15	2s	0.045	
SEMiX603GAL066HDs	720	600	1.45	12	43	0.087	771	1.40	13	0.11	3s	0.04	
SEMiX402GAR066HDs	502	400	1.45	22	24	0.12	543	1.40	10	0.15	2s	0.045	
SEMiX603GAR066HDs	720	600	1.45	12	43	0.087	771	1.40	13	0.11	3s	0.04	
SEMiX202GB066HDs	272	200	1.45	6	8	0.21	291	1.40	6.5	0.27	2s	0.045	
SEMiX302GB066HDs	379	300	1.45	12	15	0.16	419	1.40	7.5	0.19	2s	0.045	
SEMiX402GB066HDs	502	400	1.45	22	24	0.12	543	1.40	10	0.15	2s	0.045	
SEMiX603GB066HDs	720	600	1.45	12	43	0.087	771	1.40	13	0.11	3s	0.04	
SEMiX101GD066HDs	139	100	1.45	3	4	0.41	151	1.40	4.5	0.51	13	0.04	
SEMiX151GD066HDs	200	150	1.45	3.8	6.1	0.29	219	1.40	5.8	0.36	13	0.04	
SEMiX201GD066HDs	258	200	1.45	5	8	0.23	284	1.40	7.5	0.28	13	0.04	
650V - IGBT4 (Trench)													
SEMiX205GARL07E3 ¹⁾	258	200	1.45	16	16	0.23	86	1.37	-	0.81	5p	0.019	
SEMiX305GARL07E3 ¹⁾	353	300	1.45	21	21	0.18	86	1.37	-	0.81	5p	0.018	
SEMiX405GARL07E3 ¹⁾	457	400	1.45	28	28	0.14	86	1.37	-	0.81	5p	0.017	
SEMiX155MLI07E4 ²⁾	187	150	1.55	1.5	8.6	0.32	145	1.40	2.3	0.51	5p	0.009	
SEMiX205MLI07E4 ²⁾	262	200	1.55	2	10	0.22	294	1.40	4.5	0.25	5p	0.005	
SEMiX305MLI07E4 ²⁾	388	300	1.55	2.5	16	0.15	294	1.40	7.7	0.25	5p	0.005	
SEMiX405MLI07E4 ²⁾	474	400	1.55	5.3	20	0.13	377	1.40	11	0.21	5p	0.004	
SEMiX305GD07E4 ¹⁾	372	300	1.55	5.5	16	0.16	335	1.40	5.2	0.25	5p	0.004	
1200V - V-IGBT													
SEMiX151GAL12Vs	231	150	1.75	19	17	0.19	189	2.14	12	0.31	1s	0.075	
SEMiX151GB12Vs	231	150	1.75	19	17	0.19	189	2.14	12	0.31	1s	0.075	
SEMiX202GB12Vs	310	200	1.75	25	24	0.14	229	2.20	15	0.26	2s	0.045	
SEMiX223GB12Vs	323	225	1.85	20	27	0.14	263	2.17	16	0.23	3s	0.04	
SEMiX302GB12Vs	448	300	1.75	37	36	0.1	356	2.14	22	0.17	2s	0.045	
SEMiX303GB12Vs	448	300	1.75	27	36	0.1	327	2.20	21	0.19	3s	0.04	
SEMiX404GB12Vs	596	400	1.75	39	52	0.075	440	2.20	34	0.14	4s	0.03	
SEMiX453GB12Vs	673	450	1.75	40	54	0.067	516	2.14	33	0.12	3s	0.04	
SEMiX603GB12Vs	800	600	1.85	50	83	0.057	516	2.42	40	0.12	3s	0.04	
SEMiX604GB12Vs	880	600	1.75	59	79	0.051	707	2.14	50	0.086	4s	0.03	

Footnotes: 1) Sample status / 2) In production new